Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1-6. Cancelled

7. (Currently Amended) A method for mitigating defect formation in a glass layer of a semiconductor device, the method comprising:

forming the glass layer upon a substrate via a first chemical vapor deposition process; and

forming a cap oxide layer upon the glass layer via a second chemical vapor deposition process, the cap oxide layer protecting the glass layer from defect formation by shielding the glass layer from moisture which ~~is present in an immediate vicinity of the cap oxide layer and which~~ would result in the formation of defects if allowed to contact the glass layer, the cap oxide layer being formed at approximately 350°C;

wherein a reactor within which the first and second chemical vapor deposition processes are performed is not broken between the first and second chemical vapor deposition processes.

8. (Currently Amended) The method as recited in claim ~~3~~7, wherein the forming of a cap oxide layer upon the glass layer comprises forming an undoped oxide layer upon the glass layer.

9. (Currently Amended) A method for mitigating defect formation in a glass layer of a semiconductor device, the method comprising:

forming the glass layer upon a substrate; and

forming a cap oxide layer upon the glass layer, the forming of a cap oxide layer comprising forming an undoped oxide layer upon a P doped oxide film, wherein a reactor within which the glass layer and the cap oxide layer are formed is not broken between the formation of the glass and cap oxide layers, the cap oxide layer being formed at approximately 350°C and

protecting the underlying glass layer from defect formation for a period of time of at least about a day.

10. (Currently Amended) A method for mitigating defect formation in a glass layer of a semiconductor device, the method comprising:

forming the glass layer upon a substrate;

forming a cap oxide layer upon the glass layer, the cap oxide layer being formed at approximately 350°C, wherein a reactor within which the glass layer and the cap oxide layer are formed is not broken between the formation of the glass and cap oxide layers; and

leaving the cap oxide layer over the glass layer for a day or longer.

11. (Currently Amended) The method as recited in claim ~~3~~10, wherein the cap oxide layer is formed to have a thickness greater than 300 Angstroms.

12. Cancelled.

13. (Currently Amended) The method as recited in claim ~~3~~10, wherein the cap oxide layer is formed by SiH4 and N2O reacting gases.

14. (Currently Amended) The method as recited in claim ~~3~~10, wherein the cap oxide layer is formed by TEOS and O2 reacting gases.

15. (Currently Amended) The method as recited in claim ~~3~~10, wherein the cap oxide layer process temperature is between approximately 350°C and approximately 600°C.

16. (Currently Amended) The method as recited in claim ~~3~~10, wherein the glass layer process temperature is between approximately 450°C and approximately 650°C.

17. (Currently Amended) The method as recited in claim ~~3~~10, wherein forming the cap oxide layer comprises forming at least one of inter-layer dielectric, inter-poly dielectric and inter-metal dielectric layers.

18-25. Cancelled.